Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = +25°C
-20V	0.3Ω @ V_{GS}= -4.5V	-0.9A
	0.5Ω @ V_{GS}= -2.5V	-0.7A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions

Features

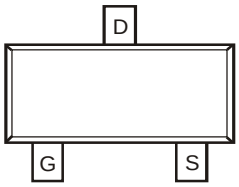
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

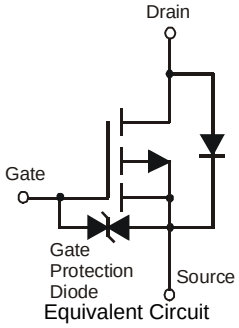
- Case: SC59
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.014 grams (approximate)

SC59

Top View



Top View
Pin-Out



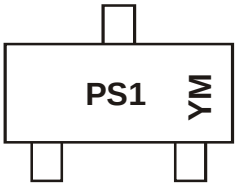
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP2012SN-7	Standard	SC59	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



PS1 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018
Code	T	U	V	W	X	Y	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±12	V
Drain Current (Note 5) Steady State	I_D	-0.7	A
Pulsed Drain Current (Note 6)	I_{DM}	-2.8	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	500	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	250	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-10	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.2	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	0.23 0.37	0.30 0.50	Ω	V_{GS} = -4.5V, I_D = -0.4A V_{GS} = -2.5V, I_D = -0.4A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	1.5	—	S	V_{DS} = -10V, I_D = -0.4A
Diode Forward Voltage (Note 7)	V_{SD}	—	-0.8	-1.1	V	V_{GS} = 0V, I_S = -0.7A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	178.5	—	pF	V_{DS} = -10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	26.3	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	18.8	—	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	—	10.4	—	ns	V_{DD} = -10V, I_D = -0.4A, V_{GS} = -5.0V, R_{GEN} = 50Ω
Turn-Off Delay Time	$t_{D(OFF)}$	—	175	—	ns	
Turn-On Rise Time	t_r	—	22.3	—	ns	
Turn-Off Fall Time	t_f	—	64	—	ns	

Notes: 5. Device mounted on FR-4 PCB.
6. Pulse width ≤10µS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.

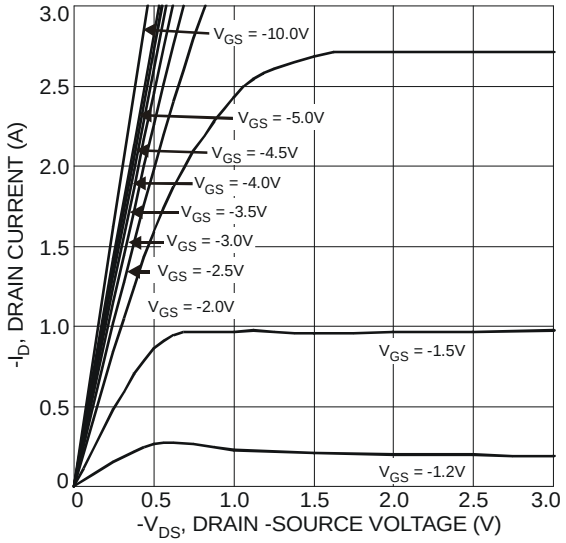


Figure 1 Typical Output Characteristics

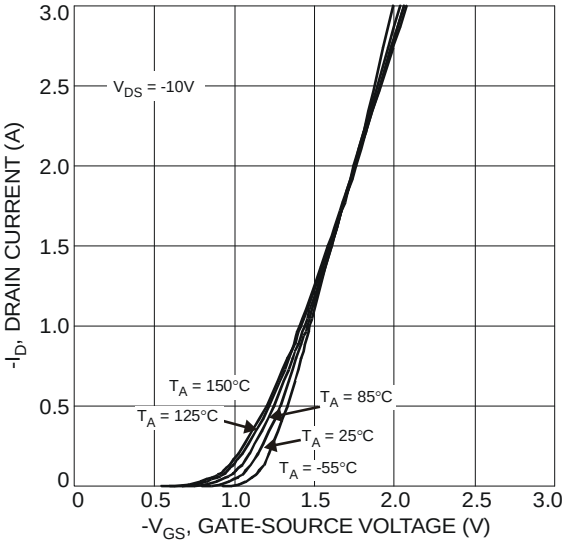


Figure 2 Typical Transfer Characteristics

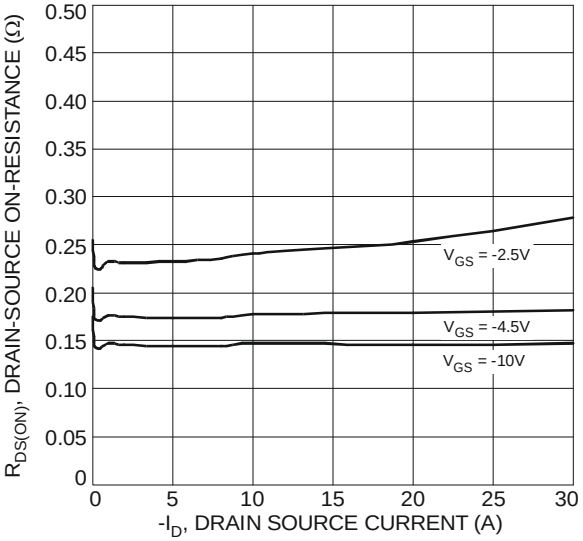


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

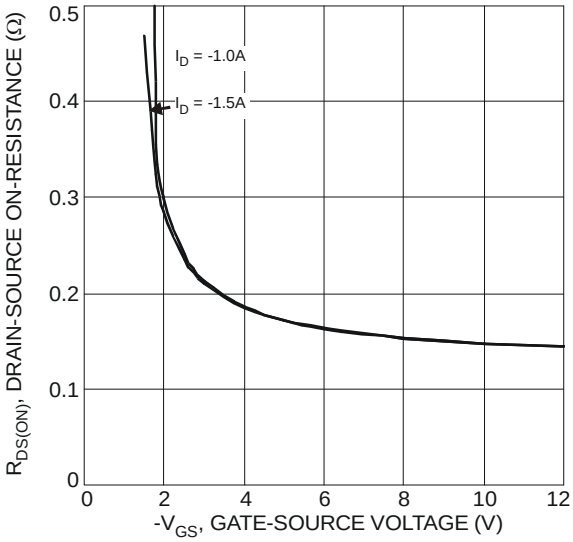


Figure 4 Typical Drain-Source On-Resistance
vs. Gate-Source Voltage

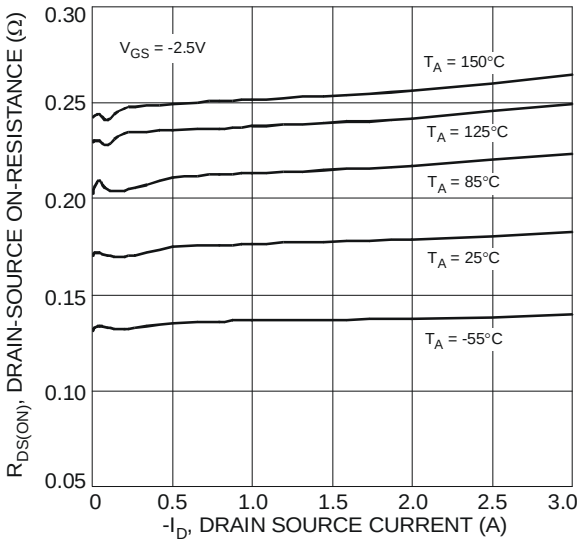


Figure 5 Typical On-Resistance vs.
Drain Current and Temperature

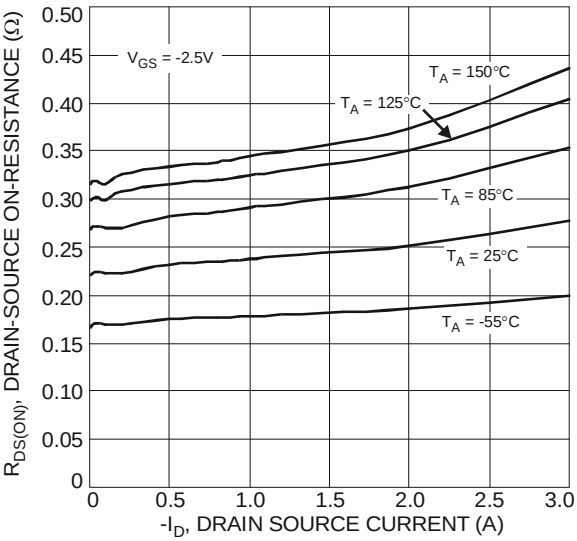


Figure 6 Typical On-Resistance vs.
Drain Current and Temperature

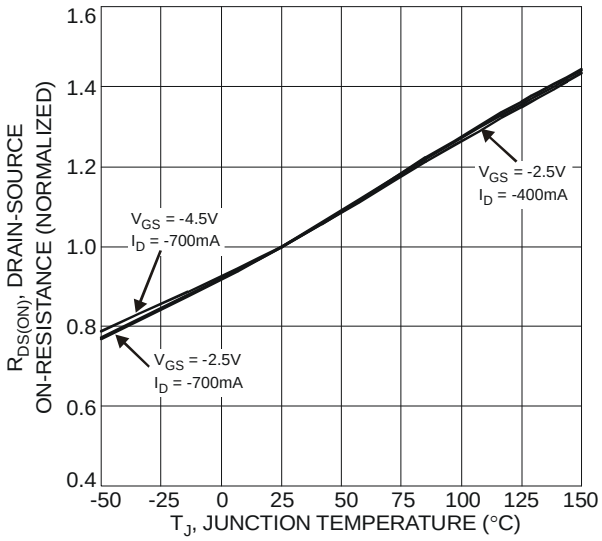


Figure 7 On-Resistance Variation with Temperature

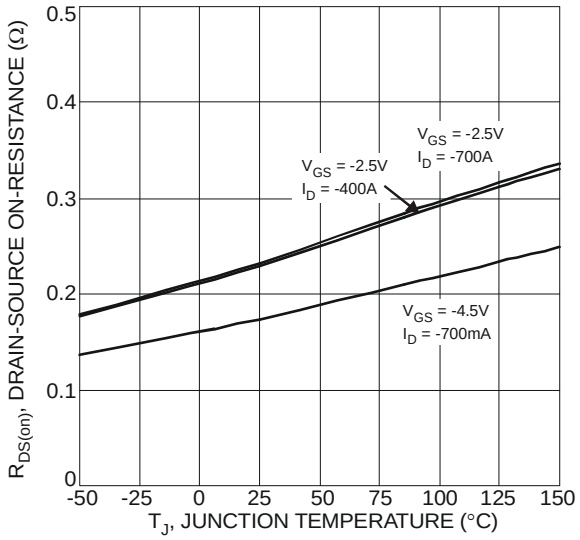


Figure 8 On-Resistance Variation with Temperature

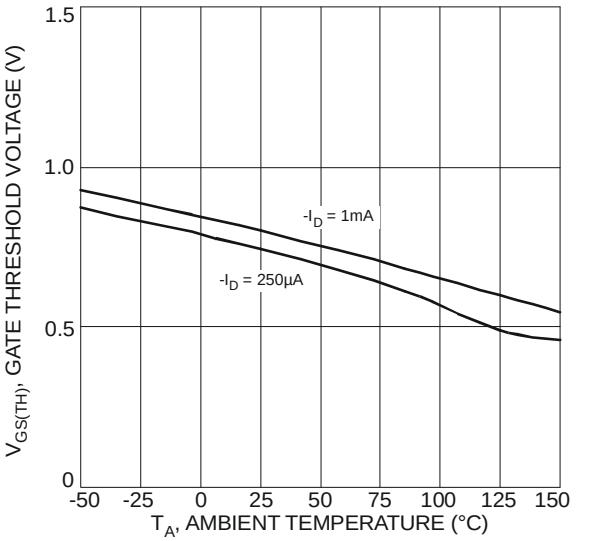


Figure 9 Gate Threshold Variation vs. Ambient Temperature

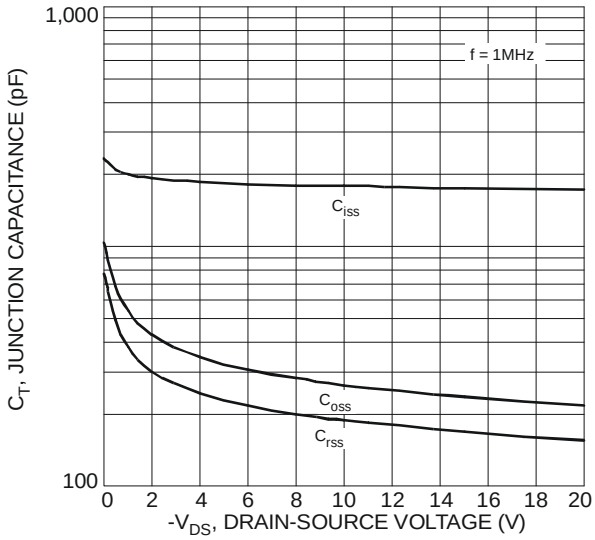
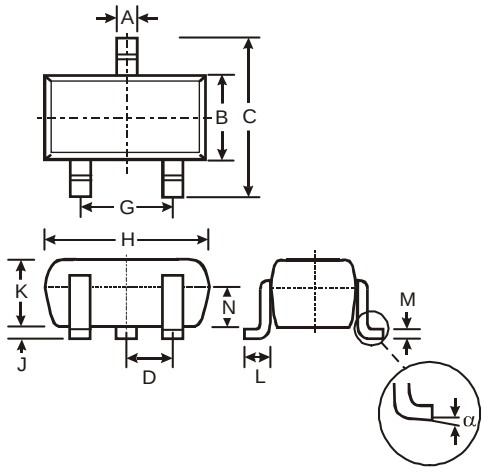


Figure 10 Typical Junction Capacitance

Package Outline Dimensions

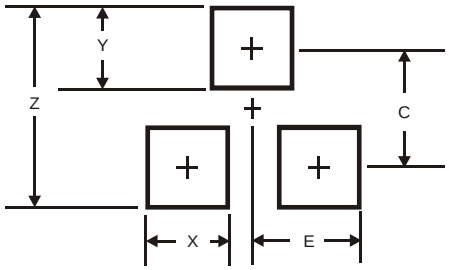
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SC59			
Dim	**Min**	**Max**	**Typ**
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	-	-	0.95
G	-	-	1.90
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
N	0.70	0.80	0.75
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.4
X	0.8
Y	1.0
C	2.4
E	1.35